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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FIS920030230US1

Application Number

Applicant(s)

Bruley et al

Filing Date

Group Art Unit

2814

*EXAMINER

INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

2002 American Institute of Physics, Volume 80, Number 17, April 29, 2002, "Application of HfSiON as a Gate Dielectric Material," Visokay et al., pp. 3183-3185.

Journal of the Korean Physical Society, Volume 37, Number 6, December 2000, "Electrical Characteristics of AlOxNy Prepared by Oxidation of Sub-10-nm-thick AlN Films for MOS Gate Dielectric Applications," Jeon et al., pp. 886-888.

IEEE PUBADDR, Piscataway, NJ, 1998 International Conference on Ion Implantation Technology, Ion Implantation Technology, Volume 2, June 1998, "Silicon-Aluminum Oxynitride Composite Films Deposited by Reactive Ion Beam Sputtering," Ogawa et al., pp. 775-778.

2002 American Institute of Physics, Volume 80, Number 17, April 29, 2002, "Suppressed Boron Penetration in p+ polycrystalline-Si/Al2O3/Si Metal-Oxide-Semiconductor Structures," Cho, et al., pp. 3177-3179.

2002 American Institute of Physics, Volume 80, Number 18, May 6, 2002, "Excellent Thermal Stability of Al2O3 Stack Structure for Metal-Oxide-Semiconductor Gate Dielectrics Application," Chang et al., pp.3385-3387.

EXAMINER

DATE CONSIDERED

7/22/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

CAPACITOR AND FABRICATION METHOD USING
ULTRA-HIGH VACUUM CVD OF SILICON NITRIDE

Application Number :

Confirmation Number:

First Named Applicant: John Bruley

Attorney Docket Number: FIS920030230US1

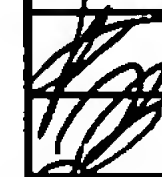


Art Unit:

Examiner:

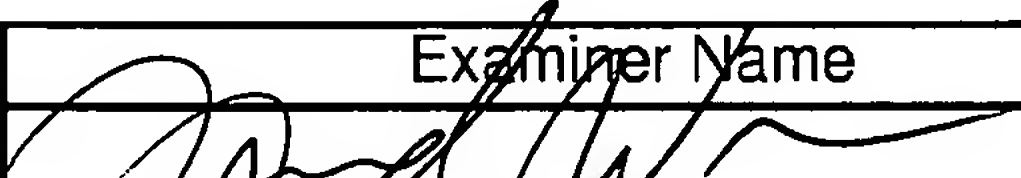
Search string: (5943560 or 5540785 or 5462883).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5943560	1999-08-24	Chang, et al.			
	2	5540785	1996-07-30	Dennard, et al.			
	3	5462883	1995-10-31	Dennard, et al.			

Signature

Examiner Name	Date
	7/22/04